



IMPORTANT NOTICE

10 December 2015

1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

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Thank you for your cooperation and understanding,

WeEn Semiconductors



1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a TO252 (DPAK) surface mountable plastic package intended for use in applications requiring high bidirectional blocking voltage, High surge current capability and high thermal cycling performance.

2. Features and benefits

- High bidirectional blocking voltage capability
- High surge current capability
- High thermal cycling performance
- Surface mountable package

3. Applications

- Ignition circuits
- Motor control
- Protection circuits
- Voltage regulation

4. Quick reference data

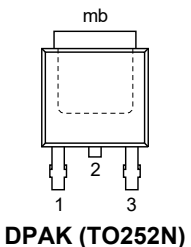

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	500	V
V_{RRM}	repetitive peak reverse voltage		-	-	500	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{mb} \leq 103\text{ °C}$; Fig. 1	-	-	7.5	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 103\text{ °C}$; Fig. 2 ; Fig. 3	-	-	12	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 10\text{ ms}$; Fig. 4 ; Fig. 5	-	-	120	A
		half sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 8.3\text{ ms}$	-	-	132	A
T_j	junction temperature		-	-	125	°C
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ °C}$; Fig. 8	-	2	15	mA
Dynamic characteristics						

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 335\text{ V}$; $T_j = 125\text{ °C}$; $R_{GK} = 100\ \Omega$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; Fig. 13	200	1000	-	V/ μ s

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	 <p style="text-align: center;">DPAK (TO252N)</p>	 <p style="text-align: center;"><i>sym037</i></p>
2	A	anode		
3	G	gate		
mb	A	mounting base; connected to anode		

6. Ordering information

Table 3. Ordering information

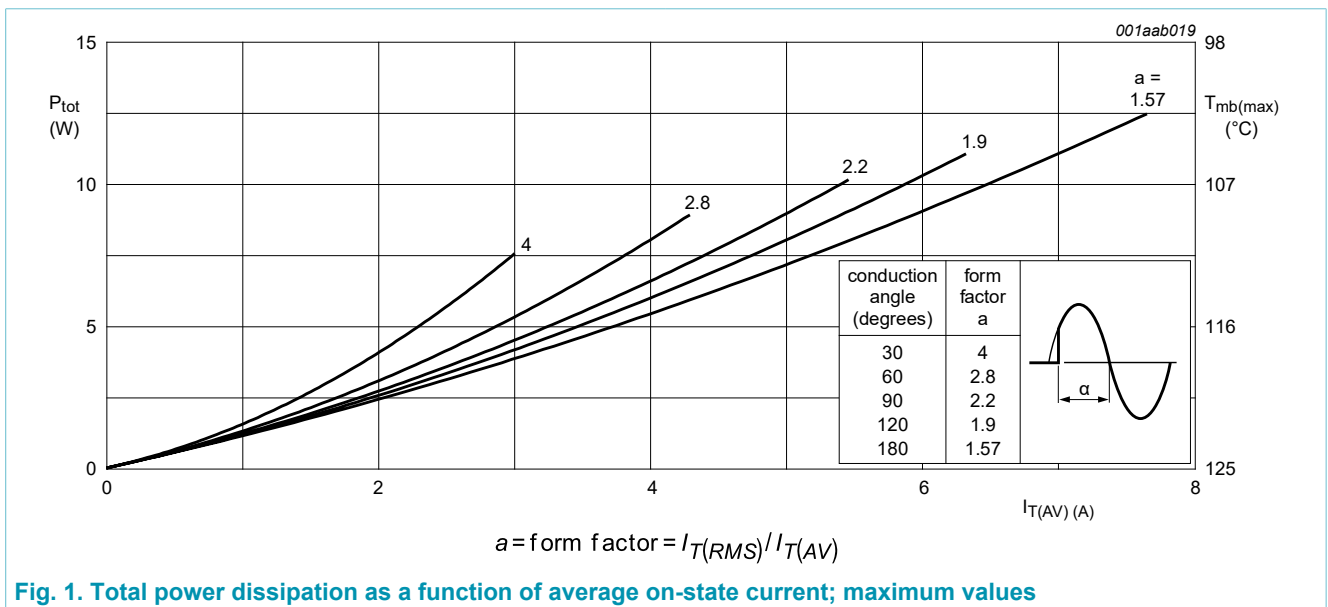
Type number	Package		
	Name	Description	Version
BT151S-500R	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	TO252N

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	500	V
V_{RRM}	repetitive peak reverse voltage		-	500	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{mb} \leq 103\text{ }^{\circ}\text{C}$; Fig. 1	-	7.5	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 103\text{ }^{\circ}\text{C}$; Fig. 2 ; Fig. 3	-	12	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 10\text{ ms}$; Fig. 4 ; Fig. 5	-	120	A
		half sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 8.3\text{ ms}$	-	132	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; SIN	-	72	A^2s
di_T/dt	rate of rise of on-state current	$I_T = 20\text{ A}$; $I_G = 50\text{ mA}$; $di_G/dt = 50\text{ mA}/\mu\text{s}$	-	50	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current		-	2	A
V_{RGM}	peak reverse gate voltage		-	5	V
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T_{stg}	storage temperature		-40	150	$^{\circ}\text{C}$
T_j	junction temperature		-	125	$^{\circ}\text{C}$



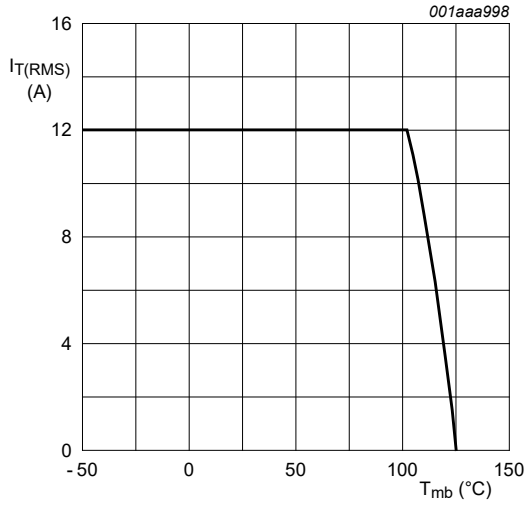
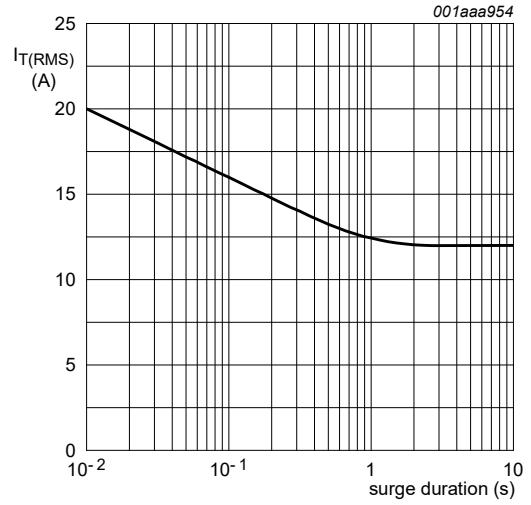


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values



$f = 50 \text{ Hz}; T_{mb} = 103 \text{ }^\circ\text{C}$

Fig. 3. RMS on-state current as a function of surge duration; maximum values

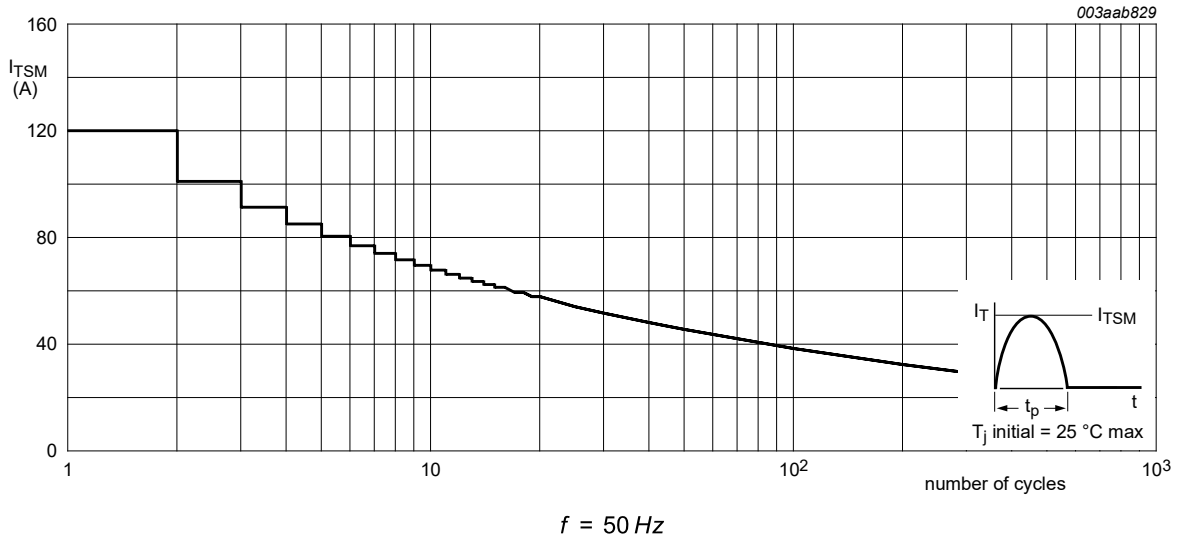
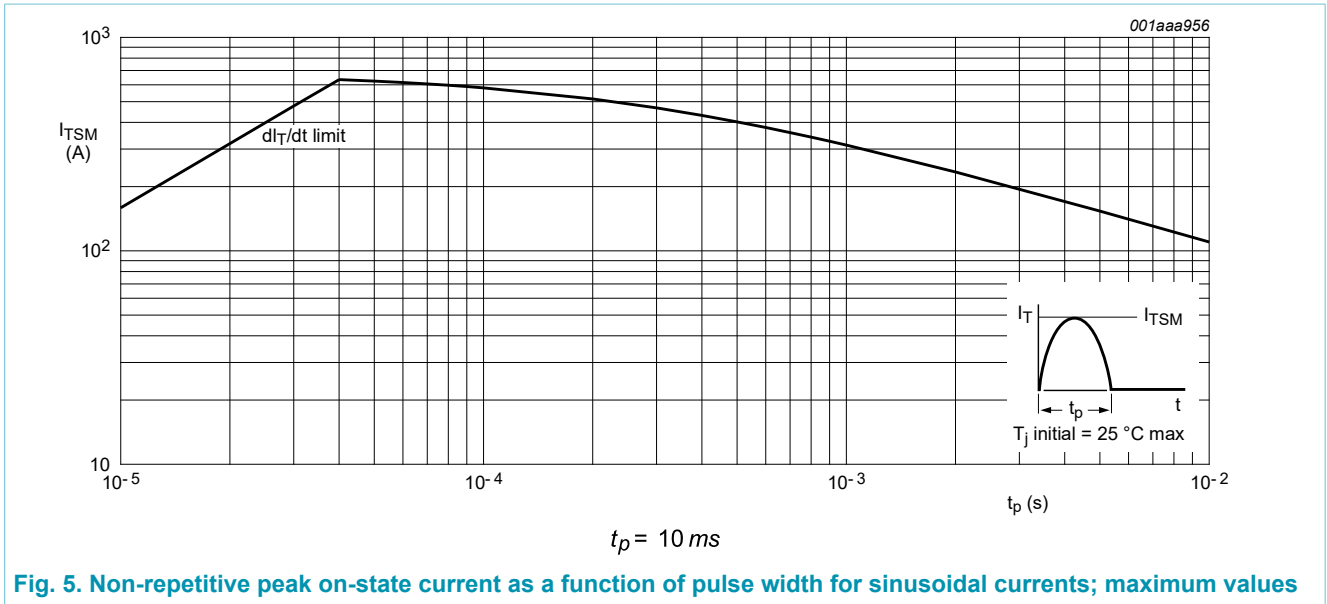


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 6	-	-	1.8	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	mounted on an FR4 printed-circuit board; Fig. 7	-	75	-	K/W

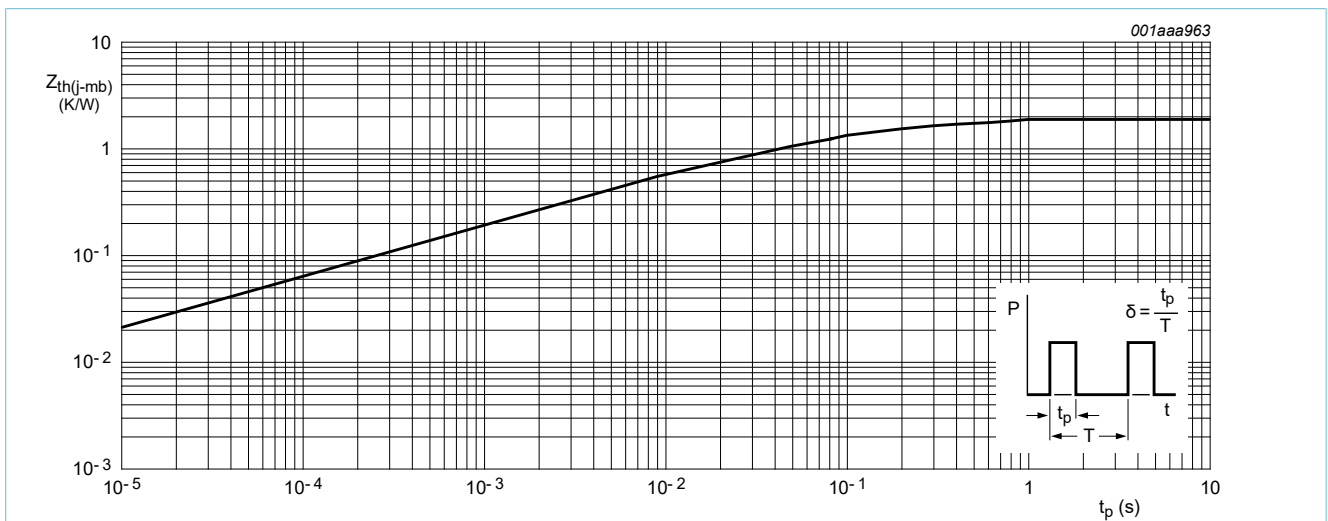


Fig. 6. Transient thermal impedance from junction to mounting base as as function of pulse width

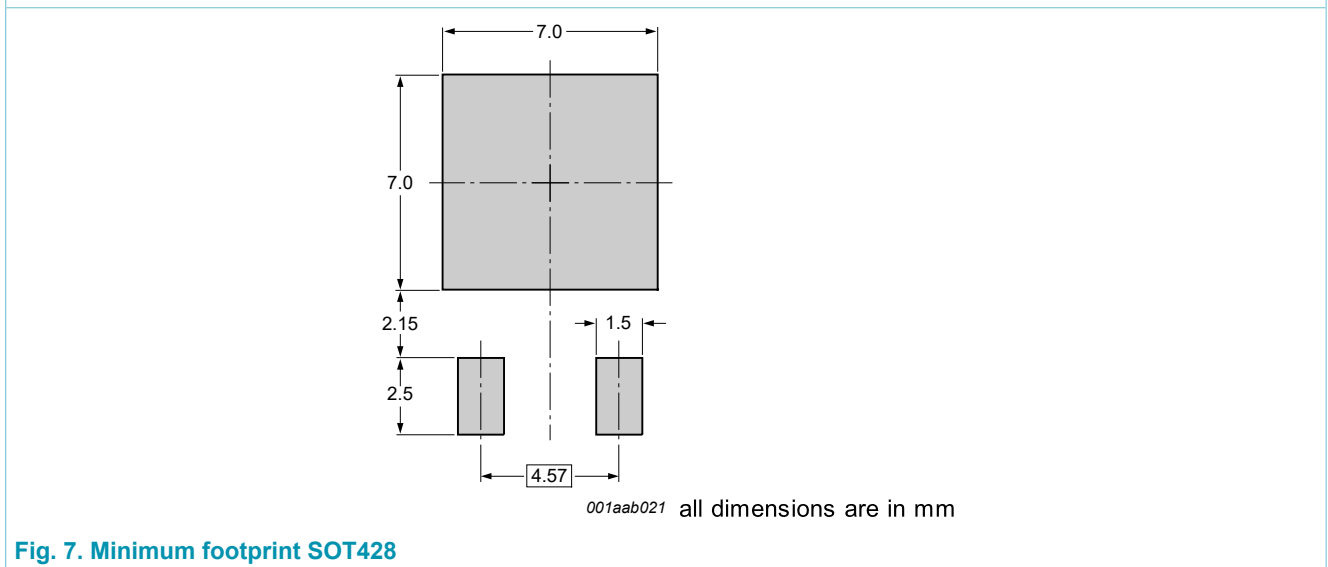
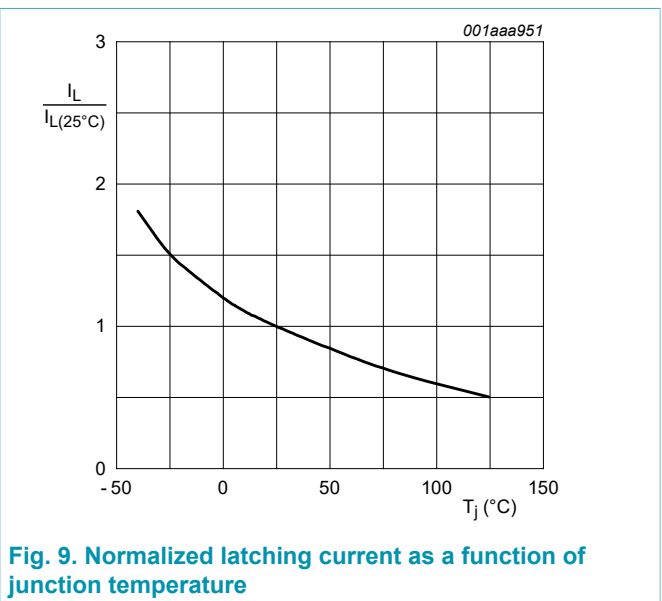
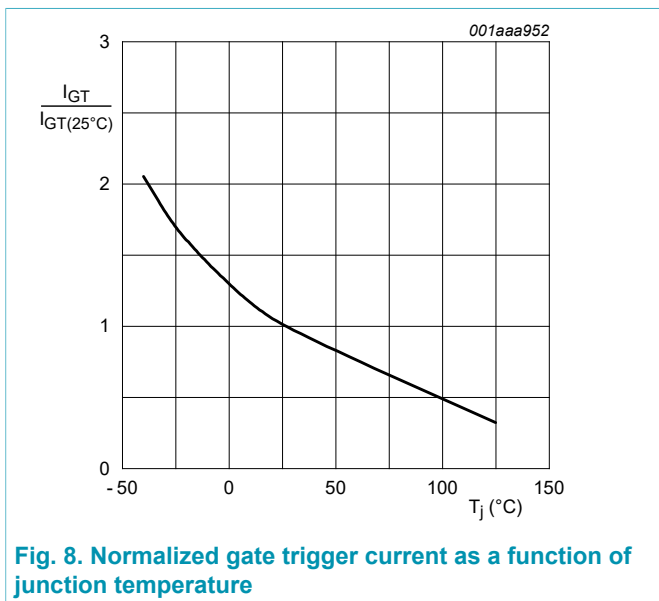


Fig. 7. Minimum footprint SOT428

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ °C}$; Fig. 8	-	2	15	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; $T_j = 25\text{ °C}$; Fig. 9	-	10	40	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ °C}$; Fig. 10	-	7	20	mA
V_T	on-state voltage	$I_T = 23\text{ A}$; $T_j = 25\text{ °C}$; Fig. 11	-	1.4	1.75	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ °C}$; Fig. 12	-	0.6	1	V
		$V_D = 500\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 125\text{ °C}$; Fig. 12	0.25	0.4	-	V
I_D	off-state current	$V_D = 500\text{ V}$; $T_j = 125\text{ °C}$	-	0.1	0.5	mA
I_R	reverse current	$V_R = 500\text{ V}$; $T_j = 125\text{ °C}$	-	0.1	0.5	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 335\text{ V}$; $T_j = 125\text{ °C}$; $R_{GK} = 100\text{ }\Omega$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; Fig. 13	200	1000	-	V/ μ s
		$V_{DM} = 335\text{ V}$; $T_j = 125\text{ °C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit; Fig. 13	50	130	-	V/ μ s
t_{gt}	gate-controlled turn-on time	$I_{TM} = 40\text{ A}$; $V_D = 500\text{ V}$; $I_G = 0.1\text{ A}$; $dI_G/dt = 5\text{ A}/\mu\text{s}$; $T_j = 25\text{ °C}$	-	2	-	μ s
t_q	commutated turn-off time	$V_{DM} = 335\text{ V}$; $T_j = 125\text{ °C}$; $I_{TM} = 20\text{ A}$; $V_R = 25\text{ V}$; $(dI_T/dt)_M = 30\text{ A}/\mu\text{s}$; $dV_D/dt = 50\text{ V}/\mu\text{s}$; $R_{GK(ext)} = 100\text{ }\Omega$; ($V_{DM} = 67\%$ of V_{DRM})	-	70	-	μ s



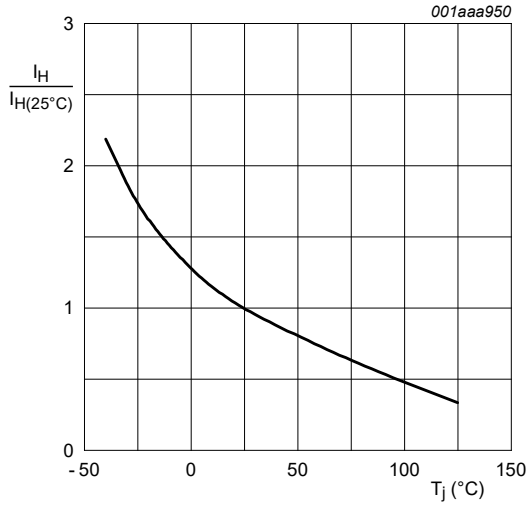
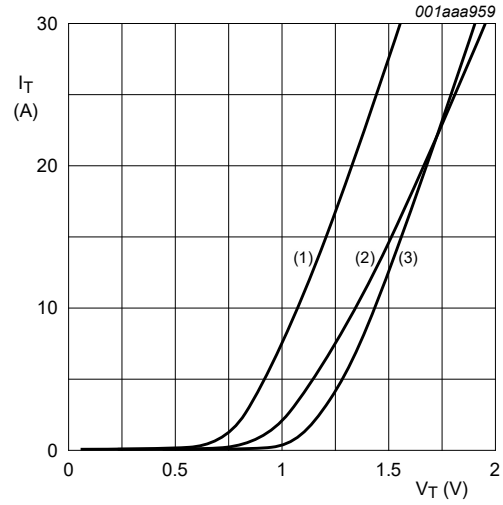


Fig. 10. Normalized holding current as a function of junction temperature



$V_o = 1.06 \text{ V}; R_s = 0.0304 \Omega$

- (1) $T_j = 125 \text{ }^\circ\text{C}$; typical values
- (2) $T_j = 125 \text{ }^\circ\text{C}$; maximum values
- (3) $T_j = 25 \text{ }^\circ\text{C}$; maximum values

Fig. 11. On-state current as a function of on-state voltage

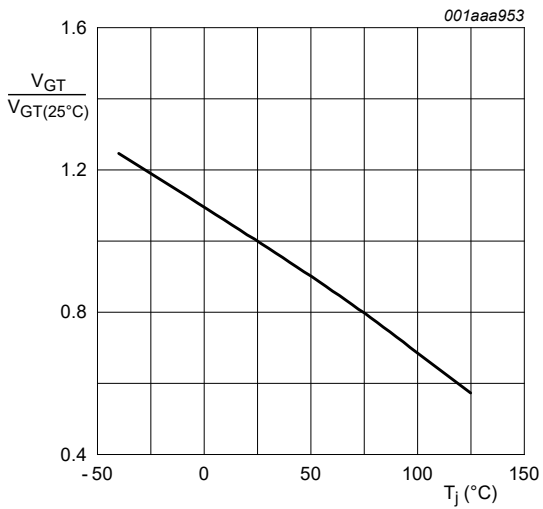
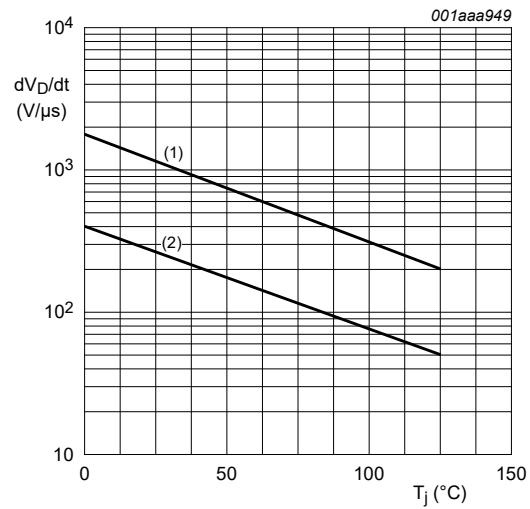


Fig. 12. Normalized gate trigger voltage as a function of junction temperature



- (1) $R_{GK} = 100 \Omega$;
- (2) gate open circuit

Fig. 13. Critical rate of rise of off-state voltage as a function of junction temperature; minimum values

10. Package outline

Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)

TO252

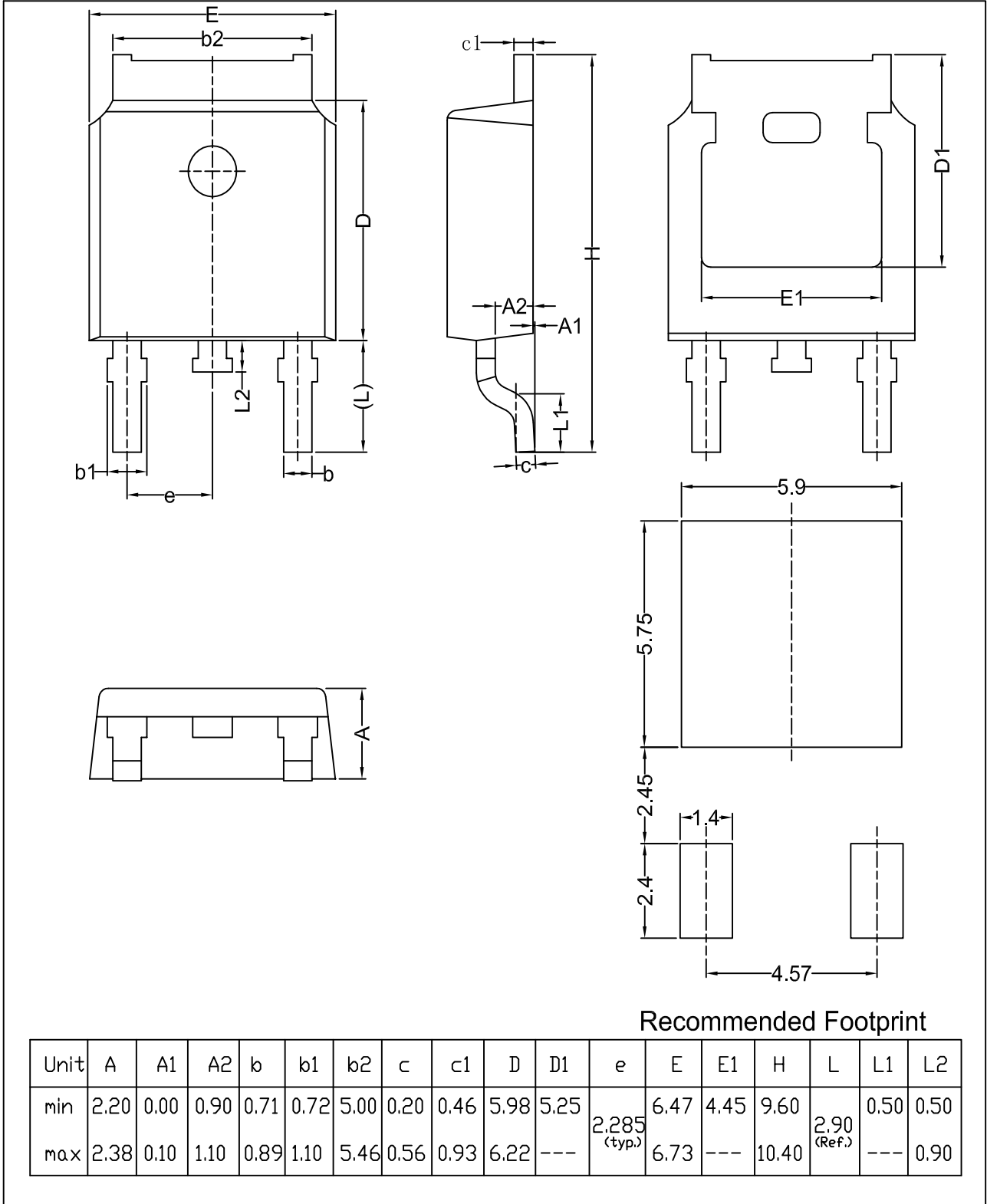


Fig. 14. Package outline DPAK (TO252N)

11. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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Date of release: 1 November 2016
